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PATENT  
Attorney Docket No. SAM-0266

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Ja-Hum Ku, et al.

Filing Date: Herewith

Title: METHOD OF FORMING A METAL GATE ELECTRODE

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Date

Amy Green

Amy Green

BOX PATENT APPLICATION

Assistant Commissioner for Patents  
Washington, DC 20231

PRELIMINARY AMENDMENT

Sir:

Prior to prosecution on the merits, please amend the application as follows:

In the Specification

Please amend the specification as follows:

Please replace the paragraph at page 9 lines 1 through 8 with the following rewritten paragraph.

*A 1* -- Fig. 3B is a cross-sectional view showing a gate metal electrode after the selective oxidation process was performed. As shown in Fig. 3B, exposed surfaces of the silicon 140, 100 are oxidized, so that silicon oxide layer 120a is formed on the surfaces of the silicon. However, the metal layers 150, 160 are minimally oxidized, so that a relatively small size metal oxide layer 120b is formed on a surface of the metal layers 150, 160. Accordingly, whiskers are not formed on the metal oxide layer 120b after the subsequent heating process. --